**IRHG57110, Radiation Test (TID) Specification Change**

**Datasheet change to match MIL-PRF-19500/743 TID test limits.**

**IRHG57110**

100V, Quad N-Channel TID Hardened MOSFET in a MO-036AB package

**RADIATION CHARACTERISTICS CHANGE:**

Table 1 Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation

- **RDS(on) Static Drain-to-Source On-State Resistance (TO-3)**
  - For up to 500K Rads(Si), change from 0.226 ohm to 0.29 ohm maximum
  - For 1000K Rads(Si), change from 0.246 ohm to 0.31 ohm maximum

- **VGS(th) Gate Threshold Voltage**
  - For 1000K Rads(Si), change from 2.0V to 1.5V minimum

Reference Datasheet PD-94432

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**APPROVING GOVERNMENT ACTIVITY**

Paul Hebert

**SIGNATURE**

October 23, 2017